

[ABSTRACT]

The purpose of the present invention is to provide a mask blank for manufacturing a transfer mask in which a thin film has high chemical resistance and film loss is minimized.

The thin film (2) includes a material containing a metal, silicon, and nitrogen; a ratio of metal content [atom%] to the total content [atom%] of metal and silicon in the thin film (2) is 15% or less; and when the thin film is subjected to an analysis of a secondary ion mass spectrometry and a distribution of a secondary ion intensity of silicon in depth direction is obtained, a ratio of a maximum peak [Counts/sec] of a secondary ion intensity of silicon at a surface layer region, which is opposite from a transparent substrate (1), of the thin film (2) divided by an average value [Counts/sec] of a secondary ion intensity of silicon in a depth direction of an inner region, which is a region excluding the surface layer region and a vicinity region with an interface, of the transparent substrate (1) of the thin film (2) is 1.6 or less.